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**PNP resistor-equipped transistor;**  $R1 = 2.2 \text{ k}\Omega$ , R2 = openRev. 1 — 12 June 2012 Product data

Product data sheet

#### **Product profile** 1.

### **1.1 General description**

PNP Resistor-Equipped Transistor (RET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

NPN complement: PDTC123TMB.

### 1.2 Features and benefits

- 100 mA output current capability
- Reduces component count
- Built-in bias resistors
- Reduces pick and place costs

### **1.3 Applications**

- Low-current peripheral driver
- Control of IC inputs

- Simplifies circuit design
- AEC-Q101 qualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Replaces general-purpose transistors in digital applications
- Mobile applications

### 1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-50	V
I <sub>O</sub>	output current		-	-	-100	mA
R1	bias resistor 1 (input)	T <sub>amb</sub> = 25 °C	1.54	2.2	2.86	kΩ



PNP resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2 = open

# 2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)		
2	G	GND (emitter)		3
3	0	output (collector)	2 Transparent top view SOT883B (DFN1006B-3)	1 2 sym009

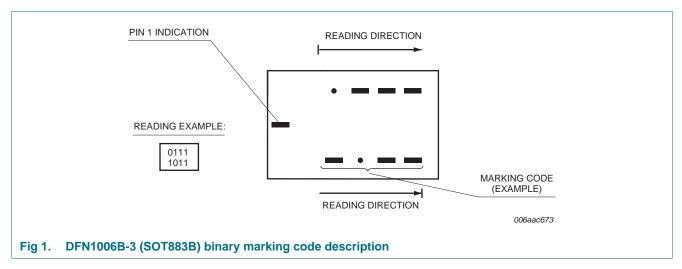
# 3. Ordering information

Table 3. Ordering information								
Type number	Package							
	Name	Description	Version					
PDTA123TMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B					

## 4. Marking

#### Table 4.Marking codes

Type number	Marking code
PDTA123TMB	0010 0011



PNP resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2 = open

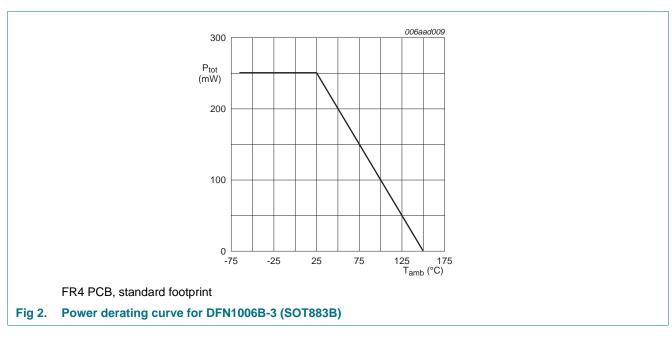
### 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
l <sub>O</sub>	output current			-	-100	mA
I <sub>CM</sub>	peak collector current	pulsed; t <sub>p</sub> ≤ 1 ms		-	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	<u>[1]</u>	-	250	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



### 6. Thermal characteristics

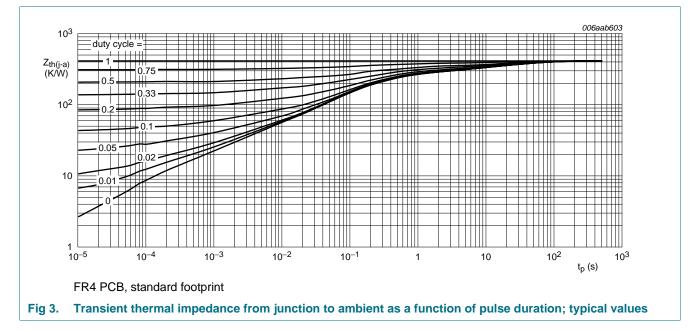
Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

### **NXP Semiconductors**

# PDTA123TMB

PNP resistor-equipped transistor;  $R1 = 2.2 \text{ k}\Omega$ , R2 = open



## 7. Characteristics

#### Table 7. Characteristics

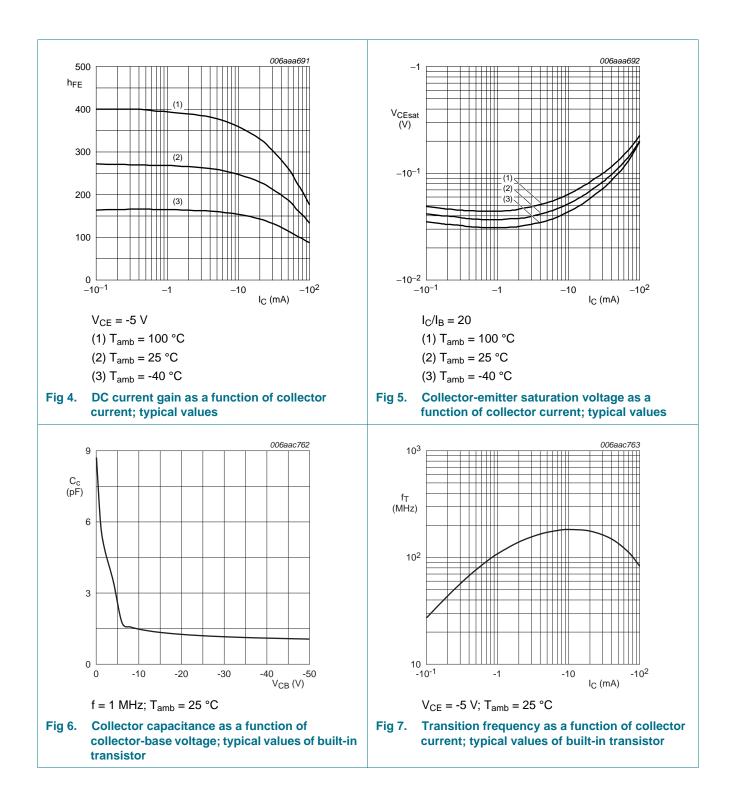
Denematen	O an allthan a		B.4.1.	<b>T</b>	N/	1.1
Parameter	Conditions		Min	тур	мах	Unit
collector-base cut-off current	$V_{CB} = -50 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$		-	-	-100	nA
collector-emitter cut-off	$V_{CE}$ = -30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	-1	μA
current	$V_{CE}$ = -30 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	-5	μA
emitter-base cut-off current	$V_{EB}$ = -5 V; $I_C$ = 0 A; $T_{amb}$ = 25 °C		-	-	-100	nA
DC current gain	$V_{CE}$ = -5 V; I <sub>C</sub> = -20 mA; T <sub>amb</sub> = 25 °C		30	-	-	
collector-emitter saturation voltage	$I_{C}$ = -10 mA; $I_{B}$ = -0.5 mA; $T_{amb}$ = 25 °C		-	-	-150	mV
bias resistor 1 (input)	T <sub>amb</sub> = 25 °C		1.54	2.2	2.86	kΩ
collector capacitance	$\label{eq:CB} \begin{array}{l} V_{CB} = -10 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \\ \text{f} = 1 \text{ MHz}; \text{ T}_{amb} = 25 \ ^{\circ}\text{C} \end{array}$		-	-	3	pF
transition frequency	$V_{CE}$ = -5 V; I <sub>C</sub> = -10 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	<u>[1]</u>	-	180	-	MHz
	current collector-emitter cut-off current emitter-base cut-off current DC current gain collector-emitter saturation voltage bias resistor 1 (input) collector capacitance	$\begin{array}{ll} \mbox{collector-base cut-off} & V_{CB} = -50 \ V; \ I_E = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C \\ \mbox{current} & V_{CE} = -30 \ V; \ I_B = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C \\ \mbox{V}_{CE} = -30 \ V; \ I_B = 0 \ A; \ T_{j} = 150 \ ^{\circ}C \\ \mbox{V}_{CE} = -30 \ V; \ I_B = 0 \ A; \ T_{j} = 150 \ ^{\circ}C \\ \mbox{V}_{CE} = -30 \ V; \ I_B = 0 \ A; \ T_{j} = 150 \ ^{\circ}C \\ \mbox{emitter-base cut-off} & V_{EB} = -5 \ V; \ I_C = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C \\ \mbox{current} & V_{CE} = -5 \ V; \ I_C = -20 \ mA; \ T_{amb} = 25 \ ^{\circ}C \\ \mbox{collector-emitter} & I_C = -10 \ mA; \ I_B = -0.5 \ mA; \ T_{amb} = 25 \ ^{\circ}C \\ \mbox{collector-capacitance} & V_{CB} = -10 \ V; \ I_E = 0 \ A; \ i_e = 0 \ A; \\ \mbox{f} = 1 \ MHz; \ T_{amb} = 25 \ ^{\circ}C \\ \mbox{transition frequency} & V_{CE} = -5 \ V; \ I_C = -10 \ mA; \ f = 100 \ mHz; \end{array}$	collector-base cut-off current $V_{CB} = -50 \text{ V}; \text{ I}_E = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ collector-emitter cut-off current $V_{CE} = -30 \text{ V}; \text{ I}_B = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ $V_{CE} = -30 \text{ V}; \text{ I}_B = 0 \text{ A}; \text{ T}_j = 150 \text{ °C}$ emitter-base cut-off current $V_{EB} = -5 \text{ V}; \text{ I}_C = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ DC current gain $V_{CE} = -5 \text{ V}; \text{ I}_C = -20 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ collector-emitter saturation voltage $I_C = -10 \text{ mA}; \text{ I}_B = -0.5 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ bias resistor 1 (input) $\text{T}_{amb} = 25 \text{ °C}$ collector capacitance $V_{CB} = -10 \text{ V}; \text{ I}_E = 0 \text{ A}; \text{ i}_e = 0 \text{ A};$ $f = 1 \text{ MHz}; \text{ T}_{amb} = 25 \text{ °C}$ transition frequency $V_{CE} = -5 \text{ V}; \text{ I}_C = -10 \text{ mA}; f = 100 \text{ MHz};$	collector-base cut-off current $V_{CB} = -50 \text{ V}; \text{ I}_E = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ -collector-emitter cut-off current $V_{CE} = -30 \text{ V}; \text{ I}_B = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ -emitter-base cut-off current $V_{CE} = -30 \text{ V}; \text{ I}_B = 0 \text{ A}; \text{ T}_j = 150 \text{ °C}$ -emitter-base cut-off current $V_{EB} = -5 \text{ V}; \text{ I}_C = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ -DC current gain $V_{CE} = -5 \text{ V}; \text{ I}_C = -20 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ 30collector-emitter saturation voltage $I_C = -10 \text{ mA}; \text{ I}_B = -0.5 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ -bias resistor 1 (input) $\text{T}_{amb} = 25 \text{ °C}$ 1.54collector capacitance $V_{CB} = -10 \text{ V}; \text{ I}_E = 0 \text{ A}; \text{ i}_e = 0 \text{ A}; _f = 1 \text{ MHz}; \text{ T}_{amb} = 25 \text{ °C}$ -transition frequency $V_{CE} = -5 \text{ V}; \text{ I}_C = -10 \text{ mA}; \text{ f} = 100 \text{ MHz};$ 11	collector-base cut-off current $V_{CB} = -50 \text{ V}; \text{ I}_E = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ collector-emitter cut-off current $V_{CE} = -30 \text{ V}; \text{ I}_B = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ witter-base cut-off current $V_{CE} = -30 \text{ V}; \text{ I}_B = 0 \text{ A}; \text{ T}_j = 150 \text{ °C}$ emitter-base cut-off current $V_{EB} = -5 \text{ V}; \text{ I}_C = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ DC current gain $V_{CE} = -5 \text{ V}; \text{ I}_C = -20 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ 30-collector-emitter saturation voltage $I_C = -10 \text{ mA}; \text{ I}_B = -0.5 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ bias resistor 1 (input) $\text{T}_{amb} = 25 \text{ °C}$ 1.542.2collector capacitance $V_{CB} = -10 \text{ V}; \text{ I}_E = 0 \text{ A}; \text{ i}_e = 0  A$	collector-base cut-off current $V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ -       -       -       -100         collector-emitter cut-off current $V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ -       -       -       -1         vertice $V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ -       -       -       -1         vertice $V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}; T_j = 150 \text{ °C}$ -       -       -5         emitter-base cut-off current $V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ -       -       -100         DC current gain $V_{CE} = -5 \text{ V}; I_C = -20 \text{ mA}; T_{amb} = 25 \text{ °C}$ -       -       -100         DC current gain $V_{CE} = -5 \text{ V}; I_C = -20 \text{ mA}; T_{amb} = 25 \text{ °C}$ 30       -       -         collector-emitter saturation voltage $I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$ -       -       -150         bias resistor 1 (input) $T_{amb} = 25 \text{ °C}$ 1.54       2.2       2.86         collector capacitance $V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; T_{amb} = 25 \text{ °C}$ -       -       3         transition frequency $V_{CE} = -5 \text{ V}; I_C = -10 \text{ mA}; f = 100 \text{ MHz};$ 11       -       180 </td

[1] Characteristics of built-in transistor.

### **NXP Semiconductors**

# PDTA123TMB

PNP resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2 = open



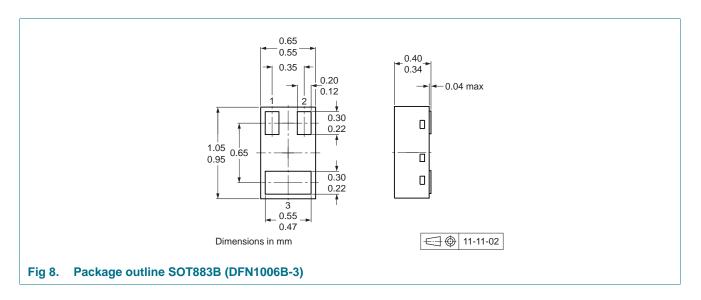
PNP resistor-equipped transistor;  $R1 = 2.2 \text{ k}\Omega$ , R2 = open

### 8. Test information

#### 8.1 Quality information

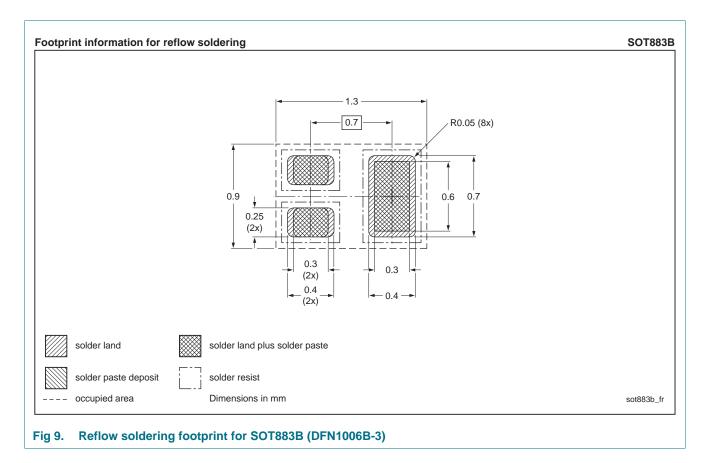
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

### 9. Package outline



PNP resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2 = open

### **10. Soldering**



PNP resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2 = open

# **11. Revision history**

Table 8. Revision	8. Revision history							
Document ID	Release date	Data sheet status	Change notice	Supersedes				
PDTA123TMB v.1	20120612	Product data sheet	-	-				

PNP resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2 = open

### 12. Legal information

#### **12.1 Data sheet status**

Document status[1] [2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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**Product data sheet** 

PDTA123TMB

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#### **PNP** resistor-equipped transistor; $R1 = 2.2 \text{ k}\Omega$ , R2 = open

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PNP resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2 = open

### 14. Contents

1.2Features and benefits.1.3Applications1.4Quick reference data2Pinning information.3Ordering information.4Marking.5Limiting values.6Thermal characteristics7Characteristics.8Test information.9Package outline10Soldering11Revision history.12Legal information.12.1Data sheet status12.3Disclaimers.12.4Trademarks.		Product profile1
1.3Applications1.4Quick reference data2Pinning information3Ordering information4Marking5Limiting values6Thermal characteristics7Characteristics8Test information9Package outline10Soldering11Revision history12Legal information12.1Data sheet status12.3Disclaimers12.4Trademarks	.1	General description1
1.4Quick reference data2Pinning information3Ordering information4Marking5Limiting values6Thermal characteristics7Characteristics8Test information8.1Quality information9Package outline10Soldering11Revision history12Legal information12.1Data sheet status12.3Disclaimers12.4Trademarks	.2	Features and benefits1
2Pinning information.3Ordering information.4Marking.5Limiting values.6Thermal characteristics7Characteristics.8Test information.8.1Quality information.9Package outline.10Soldering .11Revision history.12Legal information.12.1Data sheet status12.3Disclaimers.12.4Trademarks.	.3	Applications1
3Ordering information.4Marking.5Limiting values.6Thermal characteristics7Characteristics.8Test information.8.1Quality information9Package outline10Soldering11Revision history.12Legal information.12.1Data sheet status12.3Disclaimers.12.4Trademarks.	.4	Quick reference data1
4Marking.5Limiting values.6Thermal characteristics7Characteristics.8Test information.8.1Quality information.9Package outline10Soldering11Revision history.12Legal information.12.1Data sheet status12.2Definitions.12.3Disclaimers.12.4Trademarks.	2	Pinning information2
5Limiting values.6Thermal characteristics7Characteristics.7Characteristics.8Test information.8.1Quality information9Package outline10Soldering11Revision history.12Legal information.12.1Data sheet status12.2Definitions.12.3Disclaimers.12.4Trademarks.		Ordering information2
6Thermal characteristics7Characteristics8Test information8.1Quality information9Package outline10Soldering11Revision history12Legal information12.1Data sheet status12.2Definitions12.3Disclaimers12.4Trademarks		Marking2
<ul> <li>7 Characteristics.</li> <li>8 Test information.</li> <li>8.1 Quality information.</li> <li>9 Package outline.</li> <li>10 Soldering</li></ul>	;	Limiting values
<ul> <li>8 Test information</li></ul>	;	Thermal characteristics3
<ul> <li>8.1 Quality information</li> <li>9 Package outline</li> <li>10 Soldering</li> <li>11 Revision history</li> <li>12 Legal information</li> <li>12.1 Data sheet status</li> <li>12.2 Definitions</li> <li>12.3 Disclaimers</li> <li>12.4 Trademarks</li> </ul>	,	Characteristics4
9Package outline10Soldering11Revision history12Legal information12.1Data sheet status12.2Definitions12.3Disclaimers12.4Trademarks	;	Test information6
10Soldering11Revision history.12Legal information.12.1Data sheet status12.2Definitions.12.3Disclaimers12.4Trademarks.	5.1	Quality information6
11Revision history.12Legal information.12.1Data sheet status .12.2Definitions.12.3Disclaimers .12.4Trademarks.	)	Package outline6
12Legal information.12.1Data sheet status12.2Definitions.12.3Disclaimers.12.4Trademarks.	0	Soldering
12.1Data sheet status12.2Definitions12.3Disclaimers12.4Trademarks	1	Revision history8
12.2Definitions12.3Disclaimers12.4Trademarks	2	Legal information9
12.3Disclaimers12.4Trademarks	2.1	Data sheet status9
12.4 Trademarks	2.2	Definitions9
	2.3	Disclaimers
13 Contact information.	2.4	Trademarks10
	3	Contact information10

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